

✓ 2814#

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : H. Zhang  
Serial No.: 09/362,808  
Filed : July 28, 1999  
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICE

Art Unit : 2814  
Examiner : Thanh V. Tran

Commissioner for Patents  
Washington, D.C. 20231

TECHNOLOGY CENTER 2800

FEB 22 2002

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TRANSMITTAL LETTER AND PETITION FOR AUTOMATIC EXTENSION

Correspondence relating to this application is enclosed.  
The required fees are computed below. Please apply any charges  
not covered, or any credits, to Deposit Account No. 06-1050.

Total Claims	40	-	37	=	3	\$54
Independent	6	-	6	=	0	\$0

TOTAL FEE DUE \$54

A check for \$54 is attached.

Respectfully submitted,

Date:

8/5/08

Scott C. Harris  
Reg. No. 32,030

Fish & Richardson P.C.  
PTO Customer No. 20985  
4350 La Jolla Village Drive, Suite 500  
San Diego, California 92122  
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February 5, 2002

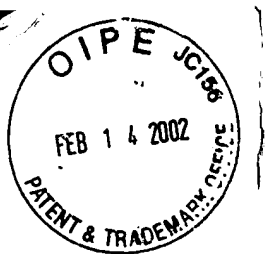
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Signature

Susan Regan

Susan Regan

Typed or Printed Name of Person Signing Certificate



Attorney's Docket No.: 07977/088002/US3155D1

#10D  
R. K. K. K.  
2/26/2002

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AMENDMENT

Sir:

In response to the Official Action mailed November 5, 2001, Paper No. 9, in the above-referenced application, please amend the above-identified application as follows.

In the Claims:

Please amend claims 1, 2, 10, 14, 19, and 24 as follows:

sub  
EX  
DI

1. (Amended) A semiconductor device comprising:  
a semiconductor having at least channel, source and drain regions;  
an insulating film formed on said semiconductor;  
a first interlayer insulating film over said insulating film;

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*Susan Regan*

Susan Regan

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